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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.		
10/044,178	01/10/2002	Todd Edgar	MIO 0011 N2 3193			
75	90 10/13/2004	EXAMINER				
Killworth, Gottman, Hagan & Schaeff, L.L.P.			LE, THAO X			
Suite 500						
One Dayton Cer	ntre	ART UNIT	PAPER NUMBER			
Dayton, OH 45402-2023			2814			
			DATE MAILED: 10/13/2004	DATE MAILED: 10/13/2004		

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary		Application	on No.	Applicant(s)			
		10/044,17	8	EDGAR, TODD			
		Examiner		Art Unit			
		Thao X Le		2814			
The MAILING DATE of this communication appears on the cover sheet with the correspondence address Period for Reply							
THE - Exte after - If the - If NC - Failu Any	ORTENED STATUTORY PERIOD FOR F MAILING DATE OF THIS COMMUNICAT nsions of time may be available under the provisions of 37 (SIX (6) MONTHS from the mailing date of this communicate period for reply specified above is less than thirty (30) days period for reply is specified above, the maximum statutory tre to reply within the set or extended period for reply will, by reply received by the Office later than three months after the ed patent term adjustment. See 37 CFR 1.704(b).	'ION. CFR 1.136(a). In no eve tion. s, a reply within the statu period will apply and will y statute, cause the appl	ent, however, may a reply be time story minimum of thirty (30) days Il expire SIX (6) MONTHS from ication to become ABANDONE	nely filed s will be considered timely. the mailing date of this cor O (35 U.S.C. § 133).			
Status							
1)🖂	Responsive to communication(s) filed on	15 September 2	004.				
2a)□	This action is FINAL . 2b)⊠ This action is non-final.						
3)□	,—						
	closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213.						
Disposition of Claims							
5)□ 6)⊠ 7)□	 Claim(s) 1-8 is/are pending in the application. 4a) Of the above claim(s) 6-8 is/are withdrawn from consideration. Claim(s) is/are allowed. Claim(s) 1-5 is/are rejected. Claim(s) is/are objected to. Claim(s) are subject to restriction and/or election requirement. 						
Applicat	ion Papers						
10)	The specification is objected to by the Example The drawing(s) filed on is/are: a) Applicant may not request that any objection Replacement drawing sheet(s) including the of the oath or declaration is objected to by	accepted or b) to the drawing(s) b correction is require	e held in abeyance. See ed if the drawing(s) is obj	e 37 CFR 1.85(a). ected to. See 37 CF	, ,		
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Priority under 35 U.S.C. § 119 12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some * c) None of: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received.							
Attachmen	t(s)		_				
	ce of References Cited (PTO-892)	40)	4) Interview Summary Paper No(s)/Mail Da				
3) 🛛 Infor	ce of Draftsperson's Patent Drawing Review (PTO-94 mation Disclosure Statement(s) (PTO-1449 or PTO/9 er No(s)/Mail Date <u>28 May 2003</u> .		5) Notice of Informal P 6) Other:		·152)		

DETAILED ACTION

Election/Restrictions

1. Applicant's election without traverse of claims 1-5 in the reply filed on 15 Sep 2004 is acknowledged.

Claim Rejections - 35 USC § 102

2. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 3. Claims 1-5 are rejected under 35 U.S.C. 102(b) as being anticipated by US 5028990 to Kotaki et al.

Regarding claim 1, Kotaki discloses a storage container structure in fig. 10 comprising: a substrate 1 including a semiconductor structure; an insulating overlayer 6/8 disposed over and in contact with said substrate, insulating overlayer 6/8 including a container region 9, fig. 4b/9, disposed therein, said container region defining a container cross section having container side walls, a container bottom wall, and a container interior bounded in part by said container side walls and said container bottom wall; a patterning stop region 5b, fig. 10, disposed over said substrate such that all of said container bottom wall is defined by an upper surface of said patterning stop region 5b; a charge storage lamina 12/13/14 over an interior surface of said container region 9; a contact region 16 defined by said charge storage lamina, wherein said

contact region defines a contact region cross section having contact region side walls and a contact region bottom wall, and wherein said contact region side walls and said contact region bottom wall are defined by a first surface of said charge storage lamina, fig. 10, and an electrical contact 16 in said contact region, wherein respective portions of said electrical contact and said charge storage lamina 12/13/14 occupy collectively at least a portion of said container region.

Regarding claim 2, Kotaki discloses a storage container structure in fig. 10 comprising: a substrate 1 including a semiconductor structure; a patterning stop region 5B with a lower surface substantially coplanar with the top of said substrate1, fig. 10; an insulating overlayer 6/8 over said substrate, said insulating overlayer 6/8 comprising: a lower overlayer surface 6 positioned over said substrate, wherein said lower overlayer surface is in contact with said top of said substrate, fig. 10, an upper overlayer surface, and an intermediate overlayer 8 portion defined between said lower overlayer surface 6 and upper overlayer surface; a container region 9 within said insulating overlayer 6/8, container region 9 defining a container cross section having container side walls, a container bottom wall, and a container interior bounded in part by container side walls and said container bottom wall, wherein all of container bottom wall is defined by an upper surface of said patterning stop region 5B, a charge storage lamina 12/13/14 over an interior surface of said container region 9; a contact region defined by said charge storage lamina, wherein said contact region defines a contact region cross section having contact region side walls and a contact region bottom wall, and wherein said contact region side walls and said contact region bottom wall are defined by a first surface of said charge storage lamina, and an electrical contact 16 in said contact region, wherein respective portions of said electrical

contact and said charge storage lamina occupy collectively at least a portion of said container region.

Regarding claim 3, Kotaki discloses a storage container structure comprising: a substrate 1 including a semiconductor structure, said substrate including a generally planar upper surface; an insulating overlayer 6/8 disposed over and in contact with said generally planar upper surface of said substrate 1, said insulating overlayer including a container region 9 disposed therein, said container region defining a container cross section having container side walls, a container bottom wall, and a container interior bounded in part by container side walls and said container bottom wall; a patterning stop region 5B including: a lower surface substantially coplanar with generally planar upper surface of substrate 1; and an upper surface configured such that the lowermost extension of container bottom wall does not project substantially below upper surface of said patterning stop region 5B; a charge storage lamina 12/13/14 over an interior surface of said container region 9; a contact region defined by said charge storage lamina, wherein contact region defines a contact region cross section having contact region side walls and a contact region bottom wall, and wherein contact region side walls and contact region bottom wall are defined by a first surface of charge storage lamina 12/13/14; and an electrical contact 16 in contact region, wherein respective portions of electrical contact and charge storage lamina occupy collectively at least a portion of container region 9, fig. 10.

Regarding claim 4, Kotaki discloses a storage container structure comprising: a substrate 1 including a semiconductor structure, substrate 1 including a generally planar upper surface, an insulating overlayer 6/8 disposed over and in contact with said generally planar upper surface of substrate, insulating overlayer 6/8 including a container region 9 disposed therein, container

region defining a container cross section having container side walls, a container bottom wall, and a container interior bounded in part by container side walls and said container bottom wall; a patterning stop region 5B including: a lower surface substantially coplanar with said generally planar upper surface of said substrate, fig. 10, and an upper surface substantially coplanar with said container bottom wall; a charge storage lamina 12/13/14 over an interior surface of said container region 9; a contact region defined by charge storage lamina, wherein contact region defines a contact region cross section having contact region side walls and a contact region bottom wall, and wherein contact region side walls and contact region bottom wall are defined by a first surface of charge storage lamina; and an electrical contact 16 in contact region, wherein respective portions of electrical contact 16 and charge storage lamina 12/13/14 occupy collectively at least a portion of container region, fig. 10.

Regarding claim 5, Kotaki discloses a storage container structure according to claim 4, wherein said upper surface of patterning stop region 5B is configured such that all of container bottom wall is defined by said upper surface of said patterning stop region 5B, fig. 10.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thao X Le whose telephone number is (571) 272-1708. The examiner can normally be reached on M-F from 8:00 AM - 4:30 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael M Fahmy can be reached on (571) 272 -1705. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Page 6

Thao X. Le 26 Sep 2004

LONG PHAM
PRIMARY EXAMINER